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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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09/594,091

06/15/2000

Akio Itoh

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06/02/2004

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EXAMINER

WARREN, MATTHEW E

ART UNIT

PAPER NUMBER

2815

DATE MAILED: 06/02/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/594,091

Applicant(s)

ITOH

Examiner

Matthew E. Warren

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 10 March 2004.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-12 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-12 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____ | 6) <input type="checkbox"/> Other: _____ |

DETAILED ACTION

This Office Action is in response to the Amendment filed on March 10, 2004.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1, 3, and 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Arita et al. (US 6,046,490) in view of Zhang (US 5,990,491).

Arita shows (fig. 1) a semiconductor device comprising a transistor having a first and second impurity region (3) formed in a substrate (1), and a gate electrode (5). A first insulating layer (6) covers the transistor. A capacitor (10) is formed on the insulating layer, the capacitor having a dielectric (8) formed of a high dielectric constant material (col. 8, lines 39-45), and an upper electrode (9) and lower electrode (7) with the dielectric positioned therebetween. A silicon oxide film (22) is formed over the capacitor and has its upper surface planarized. A silicon nitride oxide film (14), which contains some nitrogen, is formed on the oxide to prevent moisture from penetrating the device (col. 6, lines 10-17). A second insulating film (15) is formed between the capacitor and the silicon oxide film. Arita et al. does not specifically show that a contact is positioned above the silicon nitride film including nitrogen. Although it is well known in the art to form a contact above a passivation layer to provide electrical connection to the

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semiconductor device, Zhang shows (fig. 5) a semiconductor device having a lower oxide insulating layer (509), a passivation layer of silicon nitride (514), and a contact (510) formed over the passivation layer. The contact provides an electrical connection to the lower semiconductor components through the insulation layers (col. 7, lines 44-50). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the device of Arita by adding an upper contact above the silicon nitride passivation film as taught by Zhang to provide an electrical connection to the lower semiconductor components.

Claims 2 and 4 are rejected under 35 U.S.C. 103(a) as being unpatentable over Arita et al. (US 6,046,490) and Zhang (US 5,990,491) as applied to claim 1 above, and further in view of Singh et al. (US 5,847,464).

Arita and Zhang show of the element of the claims except the cavities formed in the silicon oxide film. Singh et al. discloses a semiconductor device comprising an interlevel dielectric layer (46) which has cavities (voids 72, 74, etc) formed throughout the layer (see fig. 3b). The cavities help lower the capacitance and ultimately helps reduce RC delay of signals along adjacent metal lines (col. 5 lines 57-67, col. 6, lines 48-64). Therefore it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the semiconductor capacitor of Arita and Zhang by forming cavities in the silicon oxide layer as taught by Singh to reduce capacitance and lower delay of signals along metal signal lines.

Claims 5, and 9-11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mochizuki et al. (US 5,990,507) in view of Arita et al. (US 6,046,490) and Zhang (US 5,990,491).

Mochizuki et al. shows (fig. 17) a semiconductor device comprising a transistor having a first and second impurity region (S, D) formed in a substrate (1), and a gate electrode (G, 4 & 5). A first insulating layer (10) covers the transistor. A capacitor is formed on the insulating layer, the capacitor having a dielectric (18) formed of a ferroelectric material, and an upper electrode (19) and lower electrode (17) with the dielectric positioned therebetween. A second insulating film (13) is formed on the capacitor. A local interconnection (22) is formed on the second insulating film for connecting the upper electrode of the capacitor to the first impurity region (S). Third insulating film (30) is formed on the local interconnection and the second insulating film. A first wiring (BL) is formed on the third insulating film and electrically connects to the second impurity region (D) via a hole which is formed in the first, second, and third insulating films. A fourth insulating film (39) is formed on the first wiring and has a planarized upper surface. The upper surface of the first insulating film is planarized. A second wiring is formed on the fourth film and connects to the first wiring via a hole formed through the fourth insulating layer (col. 24, lines 49-67). Mochizuki shows all of the elements of the claims except the third and fourth insulating films formed specifically of silicon oxide. Arita shows (fig. 1) a semiconductor device comprising a transistor having a capacitor device covered by third and fourth insulating films, which are formed of silicon oxide (col. 6, lines 1-17). A silicon nitride oxide film (14) is formed on the

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oxide. With this configuration, moisture is prevented from penetrating the device (col. 6, lines 10-17). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the insulating layers Mochizuki by forming oxide and then oxynitride as taught by Arita to prevent moisture from penetrating the device.

Mochizuki et al. and Arita et al. do not specifically show that a contact is positioned above the silicon nitride film including nitrogen. Although it is well known in the art to form a contact above a passivation layer to provide electrical connection to the semiconductor device, Zhang shows (fig. 5) a semiconductor device having a lower oxide insulating layer (509), a passivation layer of silicon nitride (514), and a contact (510) formed over the passivation layer. The contact provides an electrical connection to the lower semiconductor components through the insulation layers (col. 7, lines 44-50). Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the device of Mochizuki and Arita by adding an upper contact above the silicon nitride passivation film as taught by Zhang to provide an electrical connection to the lower semiconductor components.

Claims 6-8 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mochizuki et al. (US 5,990,507) in view of Arita et al. (US 6,046,490) and Zhang (US 5,990,491), as applied to claim 5 above, and further in view of Singh et al. (US 5,847,464).

Mochizuki, Arita, and Zhang show all of the elements of the claims except the cavities exposed from an upper surface of the insulating film. Singh et al. shows (fig. 5

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a-c) cavities (76, 78, 76", 78") in an upper insulating film (46) which are partially exposed from the film. Another insulating film (80) is formed on the first insulating (46) film to cover the cavities. The cavities help lower the capacitance and ultimately helps reduce RC delay of signals along adjacent metal lines (col. 5 lines 57-67, col. 6, lines 48-64). Therefore it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the semiconductor capacitor of Mochizuki, Arita, and Zhang by forming cavities in the silicon oxide layer as taught by Singh to reduce capacitance and lower delay of signals along metal signal lines.

Response to Arguments

Applicant's arguments with respect to claims 1-12 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire **THREE MONTHS** from the mailing date of this action. In the event a first reply is filed within **TWO MONTHS** of the mailing date of this final action and the advisory action is not mailed until after the end of the **THREE-MONTH** shortened statutory period, then the

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shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

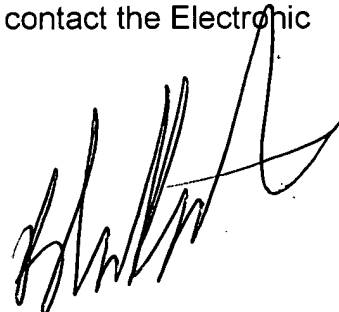
Any inquiry concerning this communication or earlier communications from the examiner should be directed to Matthew E. Warren whose telephone number is (571) 272-1737. The examiner can normally be reached on Mon-Thurs, and alternating Fri, 9:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (571) 272-1664. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

MEW

May 30, 2004



B. WILLIAM BAUMEISTER
PRIMARY EXAMINER